

**OX-043** 

Low g-Sensitivity Oven Controlled Crystal Oscillator

## a **MICROCHIP** company

## Helping Customers Innovate, Improve & Grow



### Features

- Ultra Low g-Sensitivity
- Low Phase Noise
- High Stability
- Frequency Range: 8 MHZ to 15 MHZ
- Standard Frequency 10 MHz
- Vibration Compensation

## **Applications**

- Military Avionics
- Airborne Radar
- Test Equipment
- Frequency Synthesizers
- Position Location
- Satellite Communications

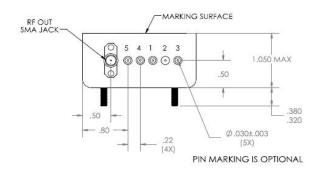
Performance Specifications						
Parameter	Min	Тур	Max	Units	Condition	
Available Frequencies						
Frequency Range	8		15	MHz		
		G-Sensi	tivity Pei	formance		
Standard crystal			1	ppb/g		
G Sensitivity w\ Low g-Crystal			0.2	ppb/g		
G Sensitivity w\ Low g-Crystal & Vibration compensation			0.02	ppb/g	Degrades to 0.2 ppb/g above 250 Hz	
(No mechanical resonances out to 2KHz)					G sensitivity specified per axis	
For oscillators with 0.1 ppb/g out to 2 KHz	contact f	factory.				
(Stabilities listed for 10 MHz. F	Frequency Stabilities <sup>1</sup> (Stabilities listed for 10 MHz. For Stabilities above 10 MHz values may degrade. Please contact factory.)					
vs. Operating Temperature Range (referenced to +25°C)	-30 -20 -10 -5		+30 +20 +10 +5	ppb ppb ppb ppb	-40 +85°C -40 +70°C -20 +70°C 0 +70°C	
Initial Tolerance vs. Supply Voltage Change vs. Load Change vs. Aging / Daily vs. Aging / 1 <sup>st</sup> Year vs. Aging / Year (following years)	-50 -2.0 -2.0 -0.5 -40 -30		+50 +2.0 +0.5 +40 +30	ppb ppb ppb ppb ppb ppb	at time of shipment, nominal EFC Vs ± 5% Load ± 5% after 72 hours of operation after 72 hours of operation	
Retrace <sup>2</sup>	-20		+20	ppb		
Warm-up Time			5	minutes	to ± 10ppb of final frequency (1 hour reading) @ +25°C	

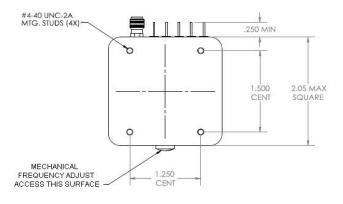
# Performance Specifications

Parameter	Min	Тур	Max	Units	Condition	
Supply Voltage (Vs)						
Supply voltage	14.25	15.0	15.75	VDC	18 & 24 VDC options available	
	11.4	12.0	12.6	VDC	18 & 24 VDC options available	
			100	Watts	during warm-up all temperatures	
			3.5	Watts	steady state @ +25°C	
Oven Power Consumption			7.0	Watts	steady state @ -40°C	
			1.0	Watts	steady state @ +70°C	
			RF Outp	ut		
Start Time		1	2	S	time required to achieve 90% of amplitude	
Signal		Sin	ewave			
Load		50		Ohm		
Output Power	+6.0	+7.0	+8.0	dBm		
Harmonics			-30	dBc		
		Freque	ncy Tun	ing (EFC)		
Tuning Range	±0.5	±0.8	±2.0	ppm	Electronic frequency control	
Linearity			20	%		
Tuning Slope		Po	ositive			
Control Voltage Range	0.0	+4.0	+8.0	VDC		
Input Impedance	20			kOhm		
Modulation Bandwidth	150			Hz		
	N	/lechani	ical Trim	(Internal)		
Tuning Range	±0.75	±1.0	±2.0	ppm	Internal Mechanical	
		P	hase No	oise		
Phase Noise <sup>3</sup> standard(@ 10 MHZ) (under static conditions - no vibration)		-100 -130 -155 -166 -168	-95 -127 -152 -163 -165	dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	1 Hz 10 Hz 100 Hz 1 KHz 10 KHz	
Phase Noise <sup>3</sup> Low Noise option (@ 10 MHZ) (under static conditions - no vibration)			-105 -135 -157 -167 -170	dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	1 Hz 10 Hz 100 Hz 1 KHz 10 KHz	

Parameter	Min	Тур	Max	Units	Condition		
Additional Parameters <sup>1</sup>							
Weight			150	g			
	Absolute Maximum Ratings						
Supply voltage (Vs)			28	V			
Output Load	25		open	ohm			
Operable Temperature Range	-55		+85	°C			
	En	vironm	ental Sp	ecificatio	ns		
Shock (Operating)	MIL-ST	0-202, Me	ethod 213	, Condition	J, 30G, 11ms, half sine		
Shock (Endurance)	Mil-STD	Mil-STD-202, Method 213, Condition C, 100G, 6ms, half sine					
Sine Vibration (Operating)	Mil-STD	Mil-STD-202, Method 204, Condition C, 10 G					
Sine Vibration (Endurance)	Mil-STD	Mil-STD-202, Method 204, Condition D, 20 G					
Random Vibration (Operating)	Mil-STD-202, Method 214, Condition I-C, 9.26 Grms, 3-5min/axis (without vibe comp) Mil-STD-202, Method 214, Condition I-A, 5.35 Grms, 3-5min/axis (with vibe comp)						
Random Vibration (Endurance)	Mil-STD	-202, Me	thod 214	, Condition	I-D, 11.95 Grms, 3hrs/axis		
Seal	Nonhermetic - Mil-STD-202, Method 112, Condition D available only as custom part number - please contact factory						
Humidity	MIL-STD-202, Method 103, Condition B, 90% rh						
Altitude	MIL-STD-202, Method 105, sea level to 30,000 ft						
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition A,B,C						
RoHS	not RoHS compliant						
Terminal Strength	MIL-STD-202, Method 211, Condition C (5 bends at 45°, 2 lbs)						
Moisture Sensitivity Level	1						
Storage Temperature Range	-55		+125	°C			

## **Outline Drawing / Enclosure**



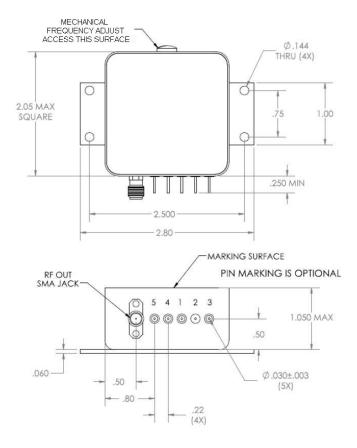


#### Dimensions in inches

Package configuration A			
ordering code	Height "H"		
5	0.80		
0	1.05		

Pin Connections						
1	Electronic Frequency Control (EFC)					
2	Ground (Case)					
3	Supply Voltage					
4	Microsemi Internal Use Only / NC					
5	Microsemi Internal Use Only / NC					

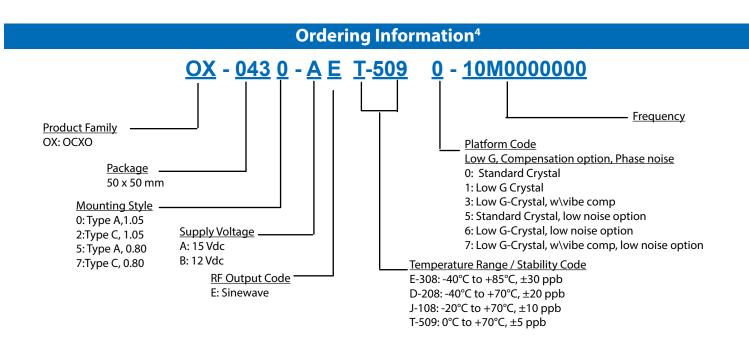
## **Outline Drawing / Enclosure**



#### Dimensions in inches

	Package	configuration C
ordering code	Height "H"	
7	0.80	
2	1.05	

Pin Connections						
1	Electronic Frequency Control (EFC)					
2	Ground (Case)					
3	Supply Voltage					
4	Microsemi Internal Use Only / NC					
5	Microsemi Internal Use Only / NC					



### **Additional Ordering Options**

Additional ordering options available include custom temperature ranges, custom temperature stabilities, custom phase noise requirements, custom height, custom supply voltage, hermetic option, and improved g-sensitvity. These modifications require a custom dash number - please contact the factory for additional information.

### **Design Tools**

Microsemi stocks the following items for small orders and prototype development:				
OX-0437-AEE-3087-10M000000				
Microsemi stocks the following evaluation board for this product:				
None				
Application Notes:				
None				

#### Notes:

- 1. Unless otherwise stated, all values are valid after warm-up time and refer to typical conditions for supply voltage, frequency control voltage, load, and temperature (25°C).
- 2. Retrace is defined as the frequency difference between the end of two 24 hour on power periods with a 24 hour off period in between while at a constant temperature.
- 3. Phase noise degrades with increasing output frequency.
- 4. Not all options and codes available at all frequencies.



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